

ABSTRACT

A semiconductor treating device (1) includes treating chamber (2) connected to a common transportation chamber (8) and treating a substrate (W) to be treated. A gas supply system (40) for supplying system (40) for supplying a predetermined gas to each of the treating chambers (2) is attached to each chamber. The gas supply system (40) has a primary side connection unit (23) connected to the source of the predetermined gas and has a flow rate control unit (13). The primary side connection unit (23) connected to the source of the predetermined gas and has a flow rate control unit (13). The primary side connection unit (23) is placed on the lower side of the corresponding treating chamber (2). The flow rate control unit (13) is placed on a gas line for supplying the gas from the primary side connection unit (23) to the corresponding treating chamber (2). The flow rate control unit (13) is provided such that at least a part of it is superposed on the upper side of the primary side connection unit (23).